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#### **60V P-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
-60V	$28m\Omega$ @ $V_{GS} = -10V$	-7A
	$35m\Omega$ @ $V_{GS} = -4.5V$	-6.2A

### **Features and Benefits**

- Low On-Resistance
- · Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

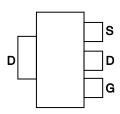
### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.112 grams (Approximate)

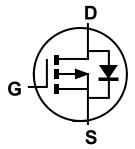




Top View



Pin Out - Top View



**Equivalent Circuit** 

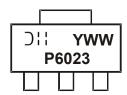
### Ordering Information (Note 4)

Ī	Part Number	Compliance	Case	Packaging
	DMP6023LE-13	Standard	SOT223	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



O':: = Manufacturer's Marking P6023 = Marking Code YWW = Date Code Marking Y or Y = Year (ex: 4 = 2014) WW = Week (01 - 53)



# 

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V <sub>DSS</sub>	-60	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Prais Current (Note E) V = 10V	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-7 -5.6	А
Continuous Drain Current (Note 5) $V_{GS} = -10V$ $T_C = +$ $T_C = +$		I <sub>D</sub>	-18.2 -14.5	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	-50	Α	
Maximum Continuous Body Diode Forward Current (Note 5)	I <sub>S</sub>	-2	Α	
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	-35.5	А	
Avalanche Energy, L = 0.1mH	Eas	62.9	mJ	

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	$P_{D}$	2 1.3	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	60	°C/W	
Total Power Dissipation (Note 5) $T_C = +25^{\circ}C$		P <sub>D</sub>	17.3	W
Thermal Resistance, Junction to Case (Note 5)	$R_{ heta JC}$	7.2	°C/W	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage		-60	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C		_	_	-1	μA	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V	
Gate-Source Leakage		_	_	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1	_	-3	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	D		28	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -5A		
Static Dialit-Source Off-Resistance	R <sub>DS(ON)</sub>	_	_	35	11177	$V_{GS} = -4.5V$ , $I_{D} = -4A$	
Diode Forward Voltage	$V_{SD}$	_	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C <sub>iss</sub>	_	2569	_	pF	V 20V V 20V	
Output Capacitance	Coss	_	179	_	pF	$V_{DS} = -30V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	143	_	pF	- I - IIVIHZ	
Gate Resistance	$R_g$	_	8	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	_	26.5	_	nC		
Total Gate Charge (V <sub>GS</sub> = -10V)		_	53.1	_	nC	\/ - 20\/ I - 5A	
Gate-Source Charge	Q <sub>gs</sub>	_	7.1	_	nC	$V_{DS} = -30V, I_{D} = -5A$	
Gate-Drain Charge	$Q_{gd}$	_	12.6	_	nC		
Turn-On Delay Time	t <sub>D(on)</sub>		6	_	ns		
Turn-On Rise Time	t <sub>r</sub>		7.1	_	ns	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -30V,	
Turn-Off Delay Time	t <sub>D(off)</sub>		110	_	ns	$R_G = 3\Omega, I_D = -5A$	
Turn-Off Fall Time	t <sub>f</sub>		62	_	ns	1	
Body Diode Reverse Recovery Time	t <sub>rr</sub>		20	_	nS	54 17/11 4004/	
Body Diode Reverse Recovery Charge		-	14	_	nC	I <sub>F</sub> = -5A, di/dt = 100A/μs	

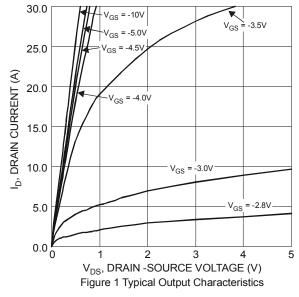
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square pad layout.

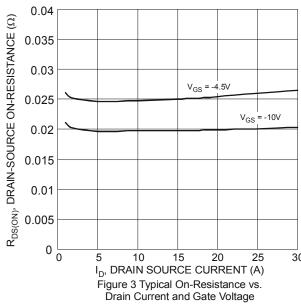
<sup>6.</sup> Short duration pulse test used to minimize self-heating effect.

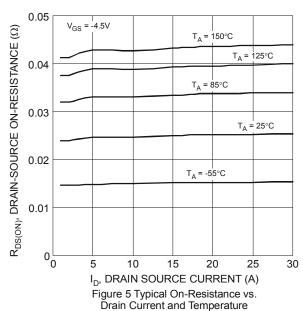
<sup>7.</sup> Guaranteed by design. Not subject to product testing.

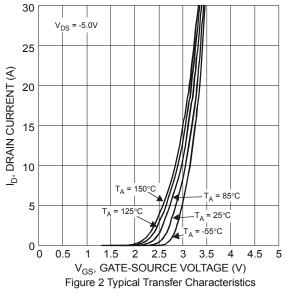


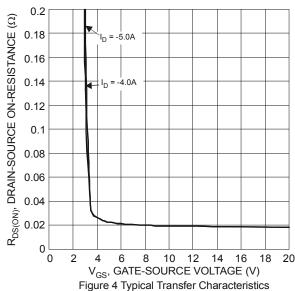


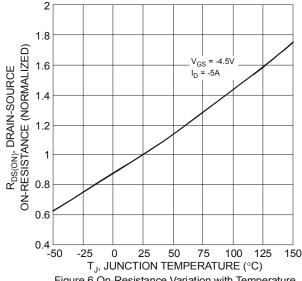




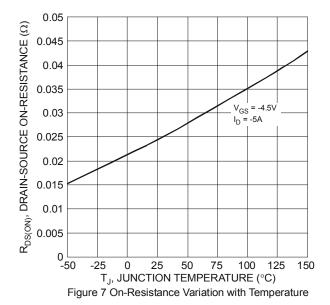


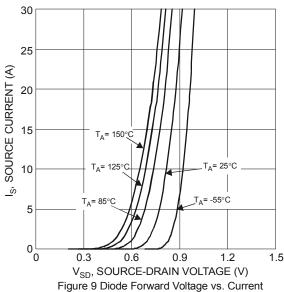


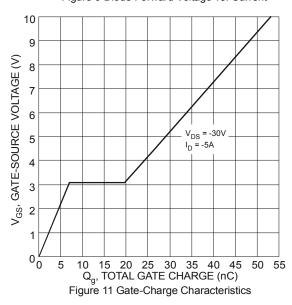












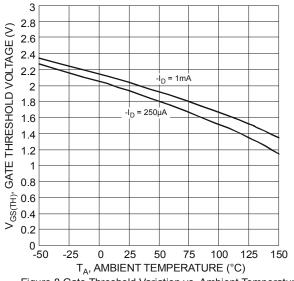
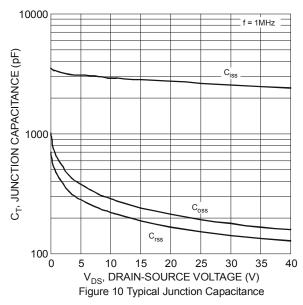
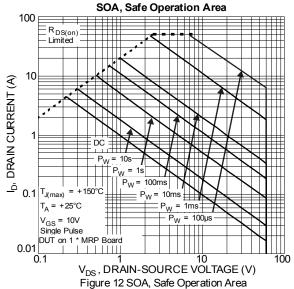


Figure 8 Gate Threshold Variation vs. Ambient Temperature

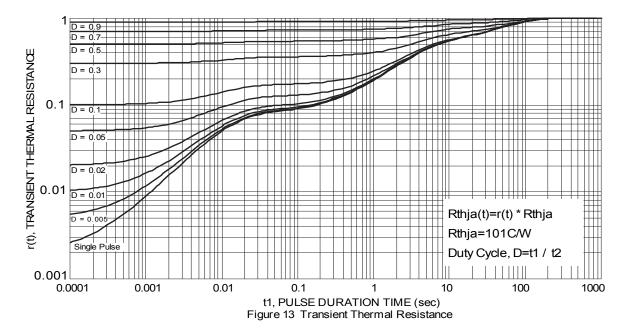




January 2015

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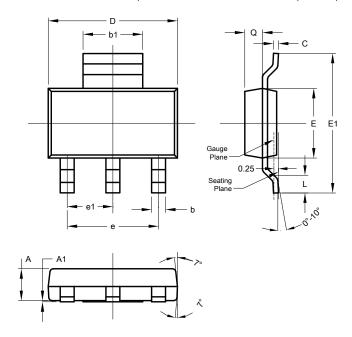






# **Package Outline Dimensions**

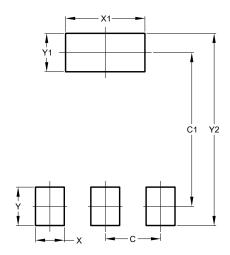
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Y	1.60		
Y1	1.60		
Y2	8.00		



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